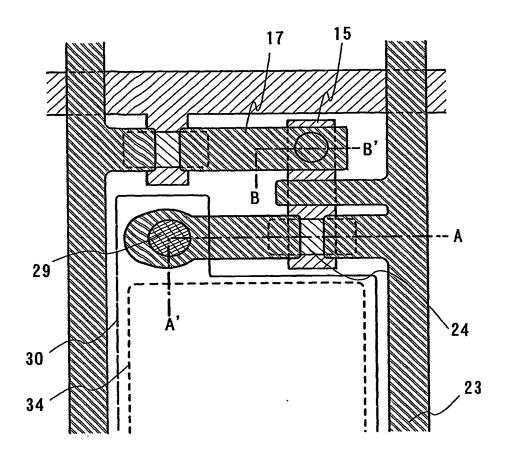
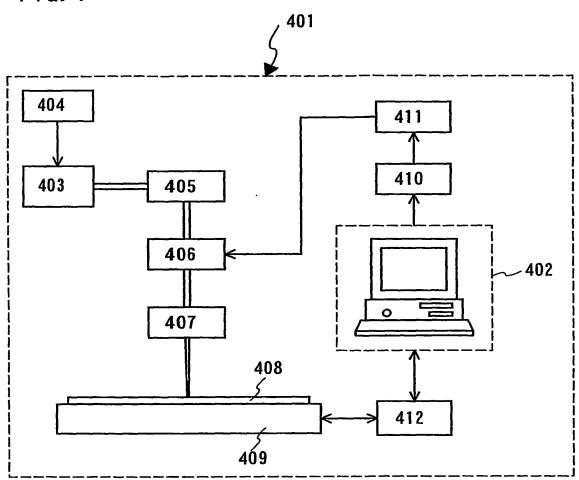


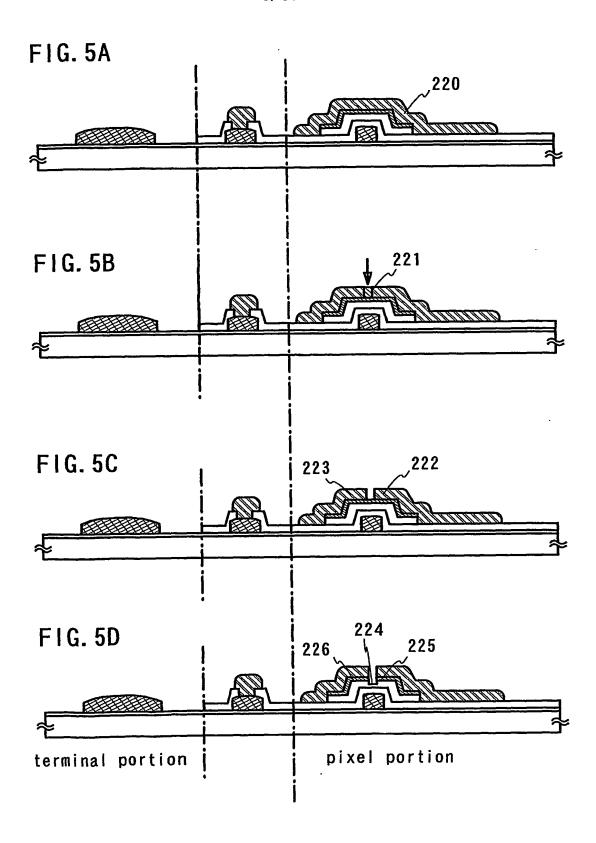
FIG. 3

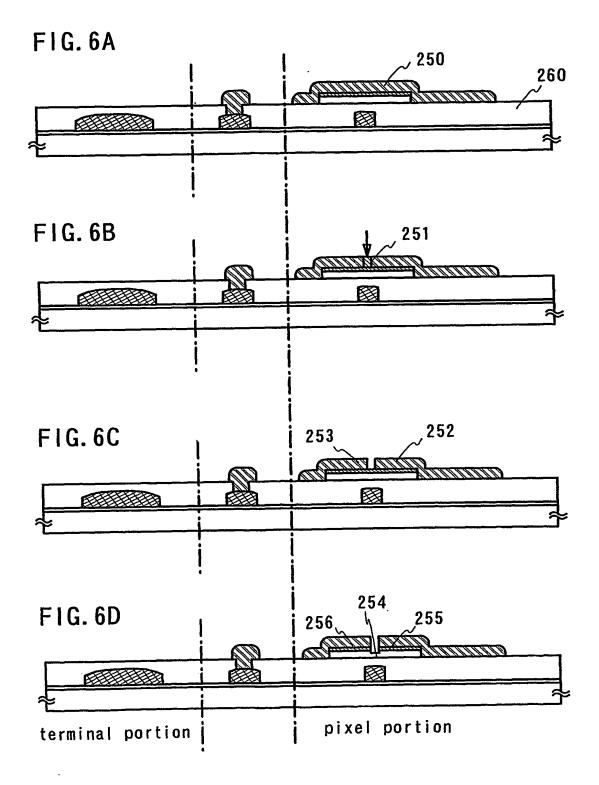


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FIG. 4







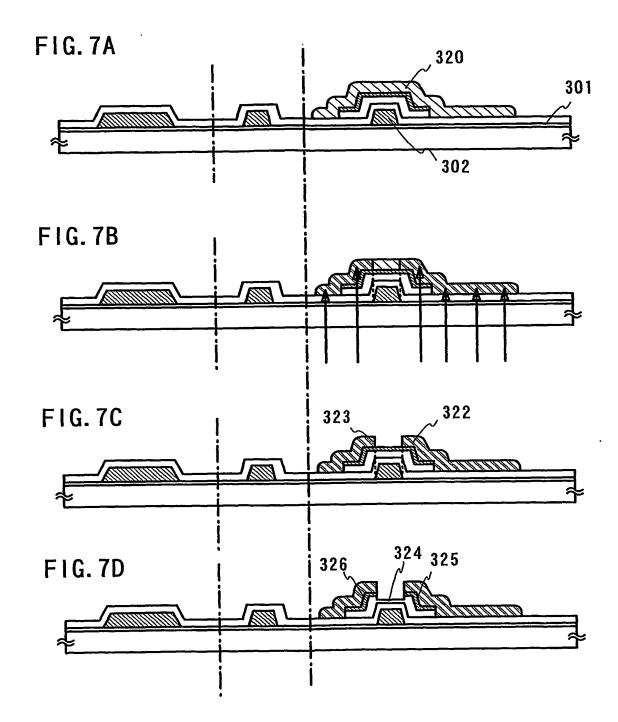


FIG. 8

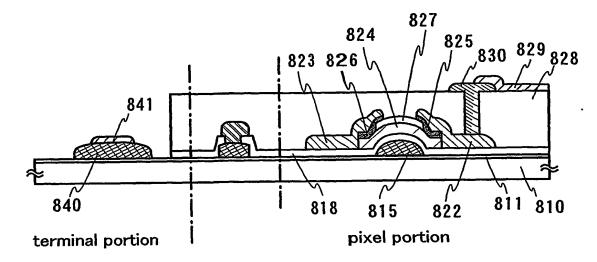
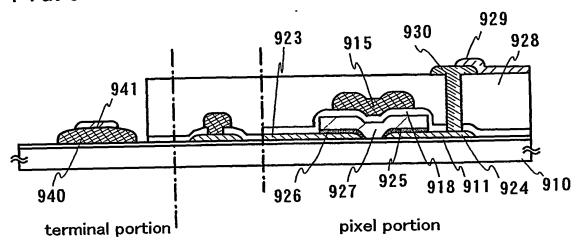
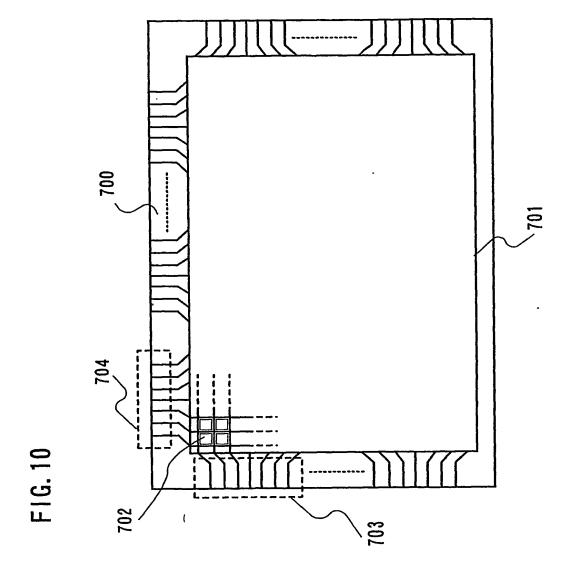
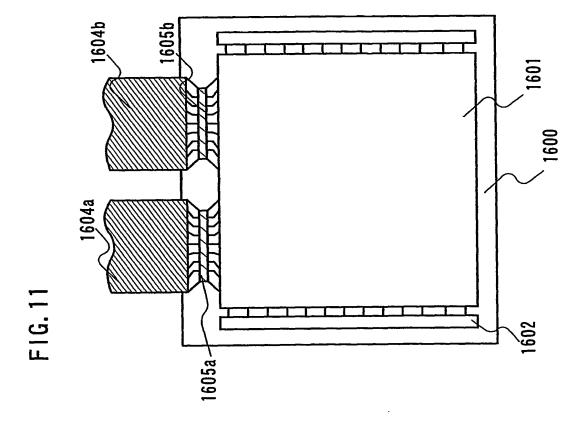


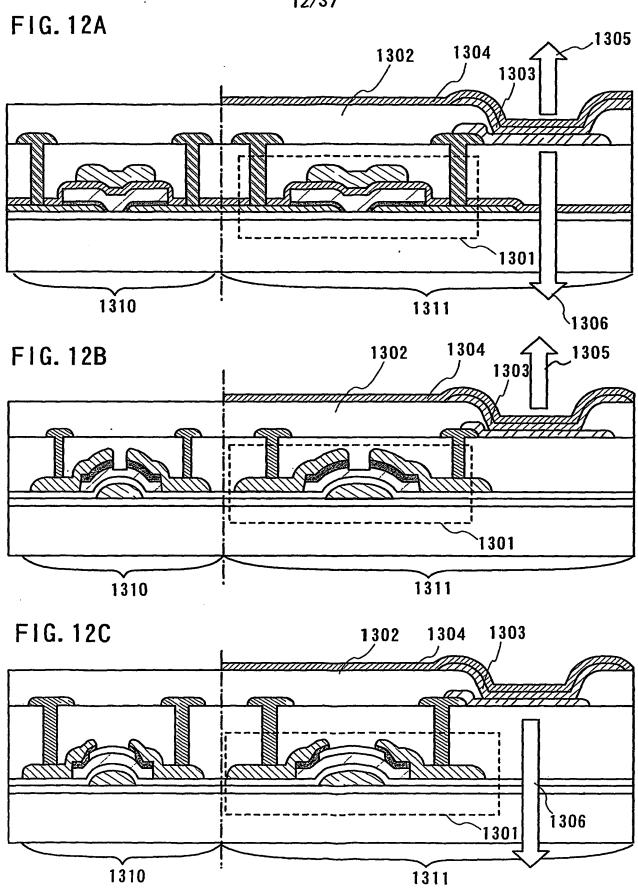
FIG. 9

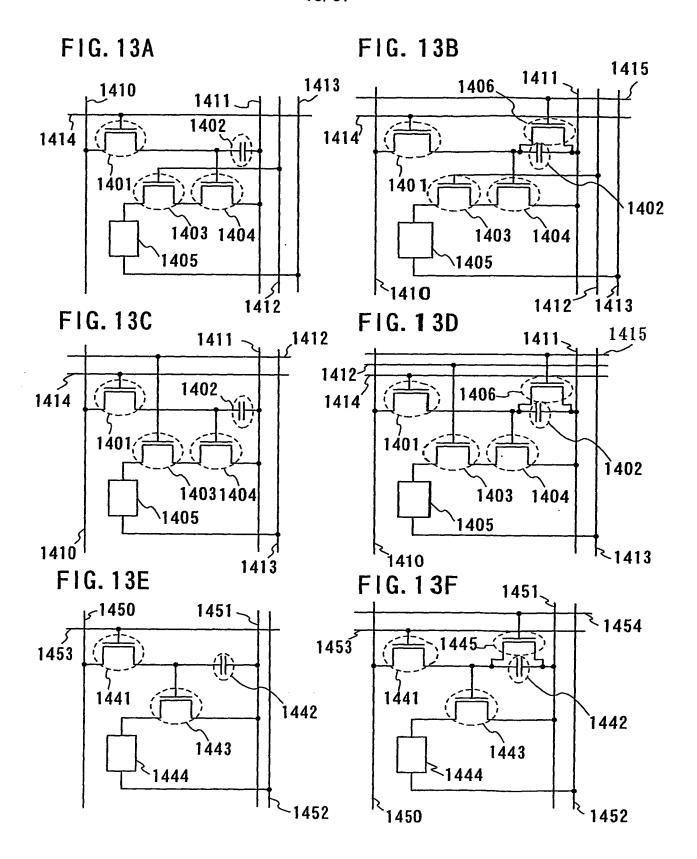




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FIG. 14A

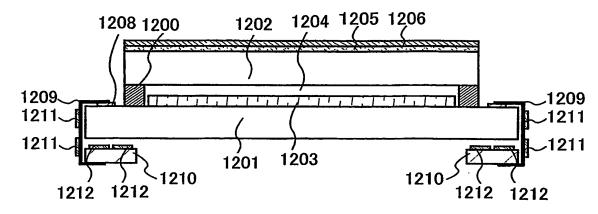


FIG. 14B

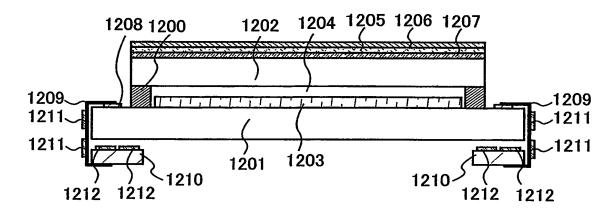
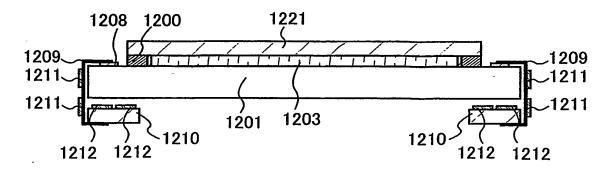


FIG. 14C



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FIG. 15A

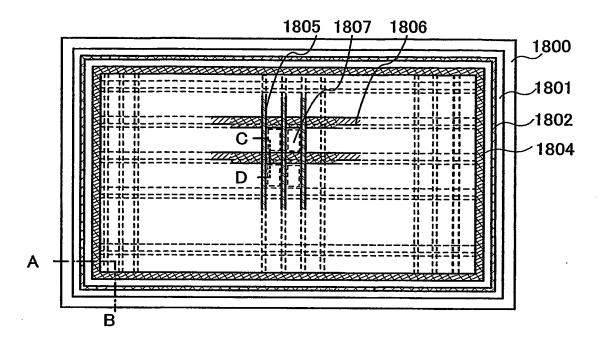


FIG. 15B

1804 1805 1812 1804

1802 1802

A 1803 B

FIG. 15C

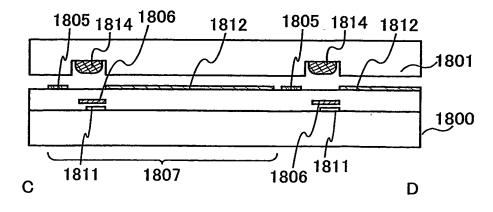
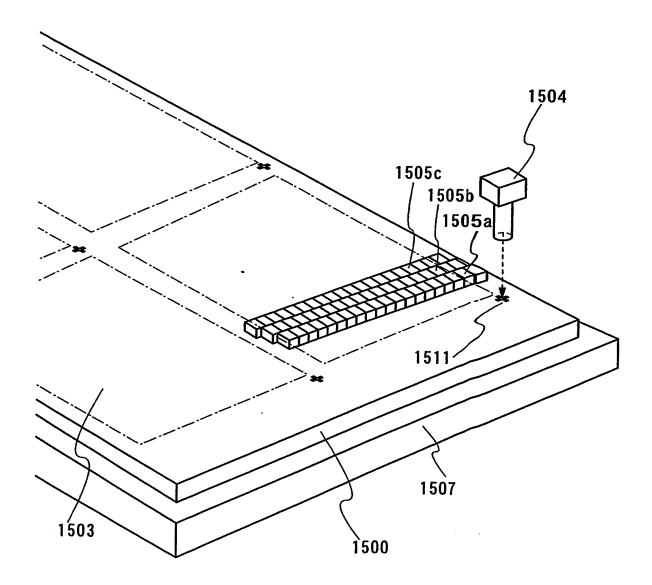
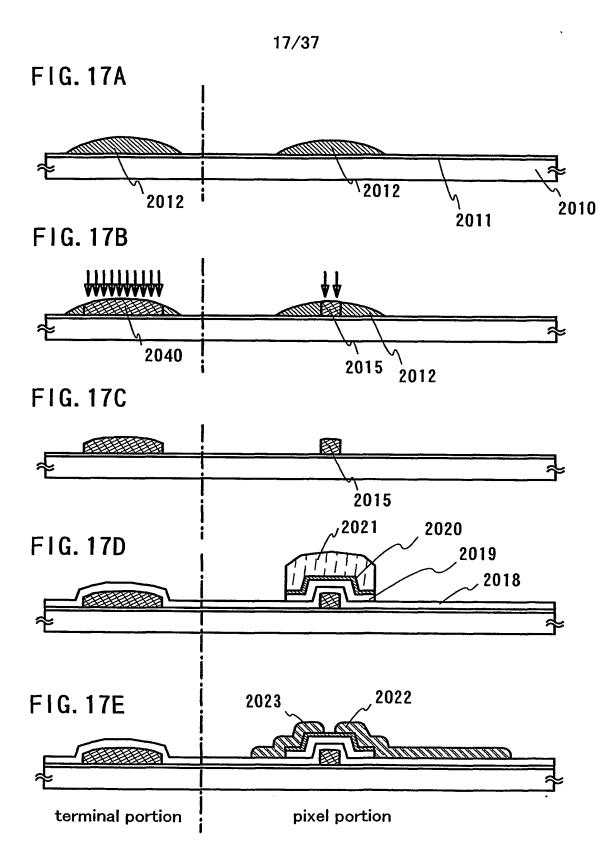


FIG. 16





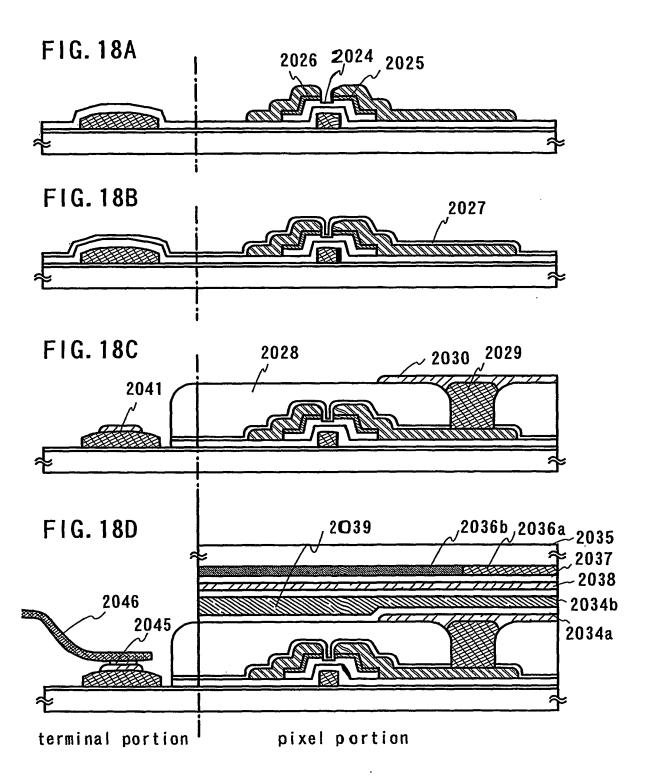
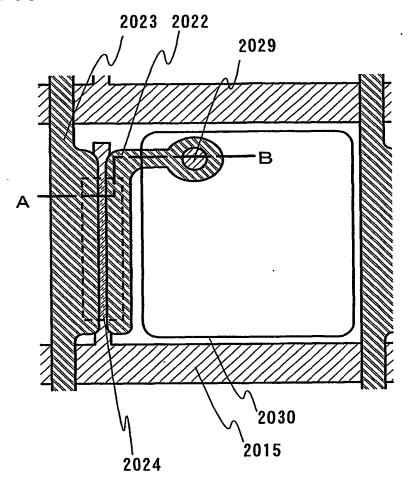


FIG. 19



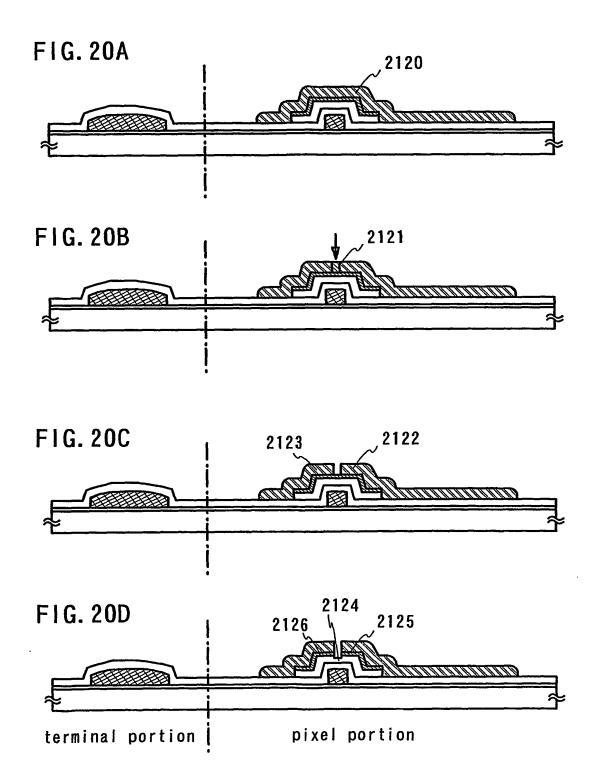


FIG. 21A

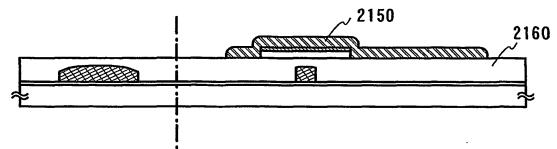
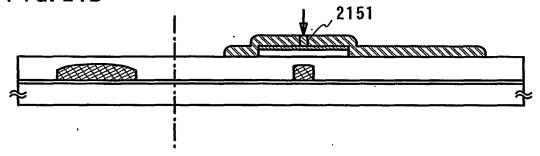


FIG. 21B



F1G. 21C

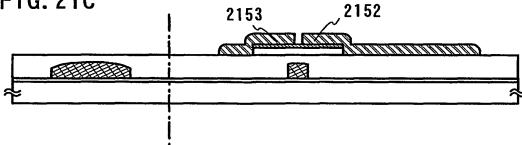
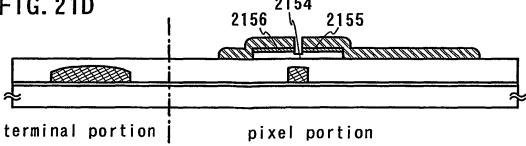
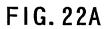


FIG. 21D



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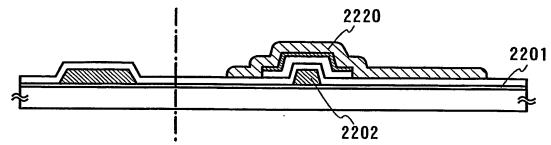


FIG. 22B

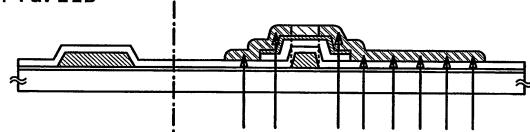


FIG. 22C

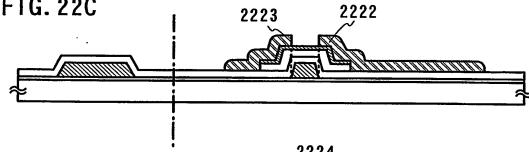


FIG. 22D

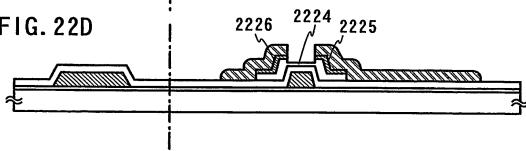


FIG. 23

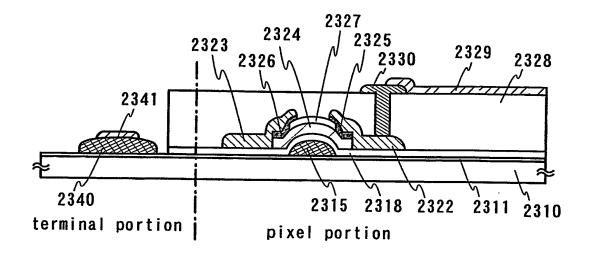
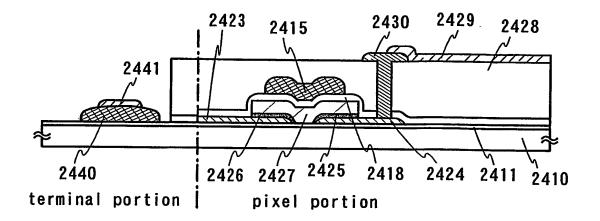


FIG. 24



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FIG. 25A

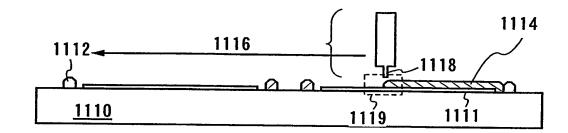
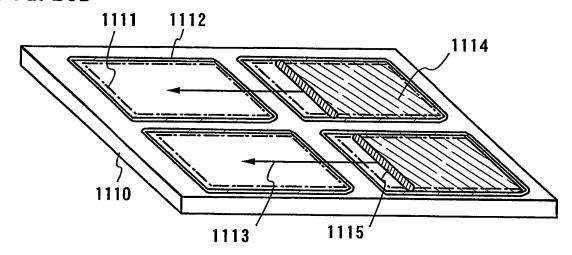
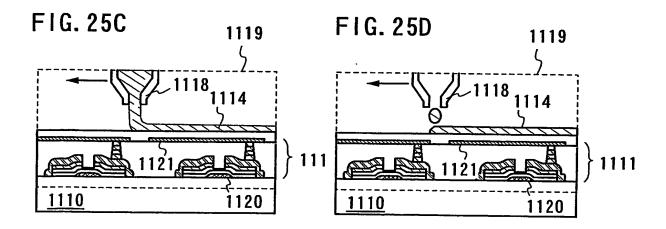


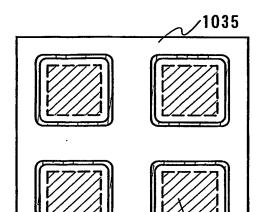
FIG. 25B





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FIG. 26A



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FIG. 26B

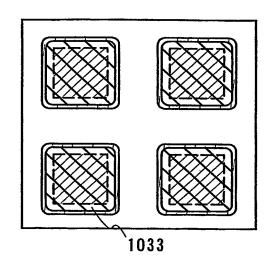


FIG. 26C

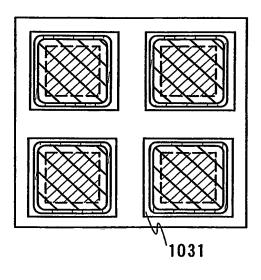
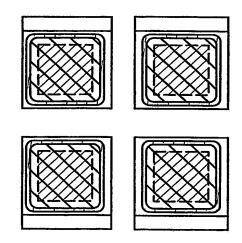
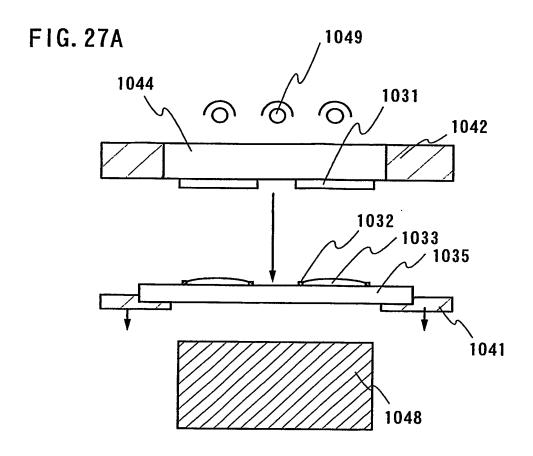
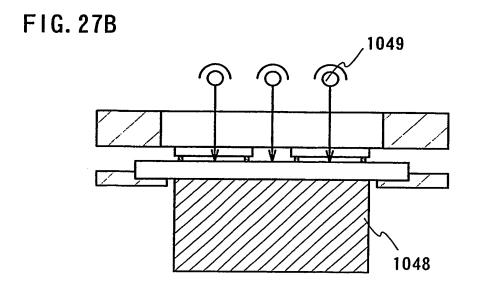


FIG. 26D

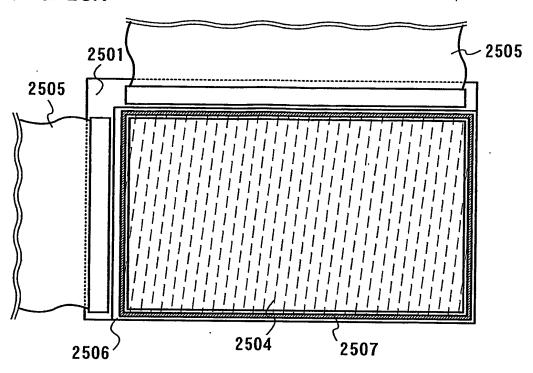






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FIG. 28A



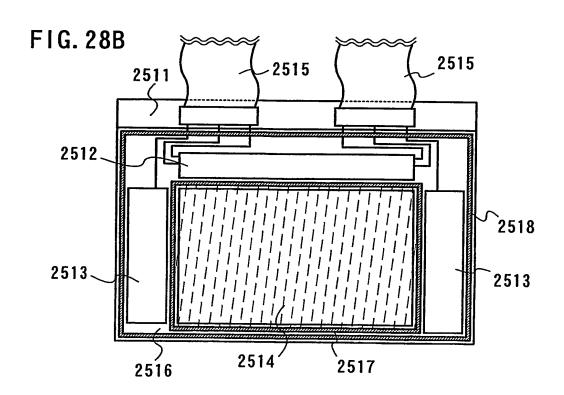


FIG. 29

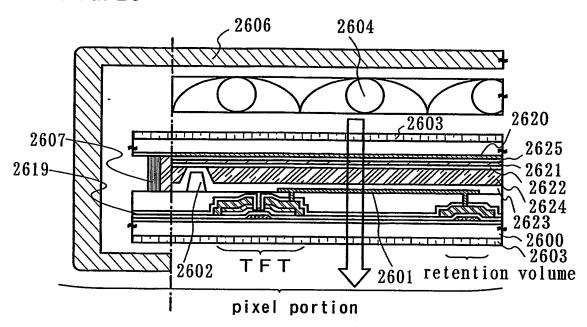


FIG. 30

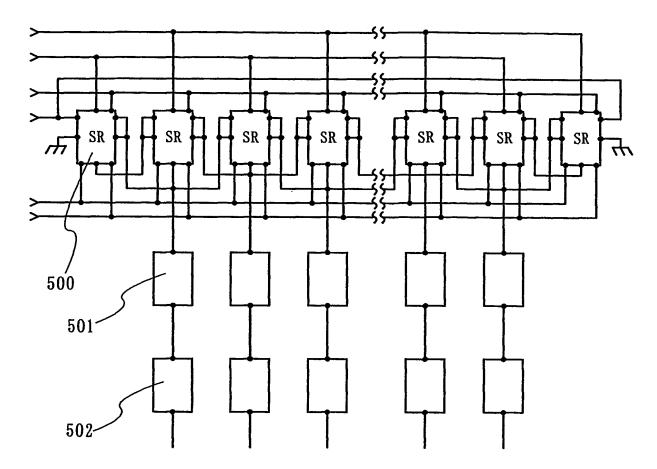


FIG. 31

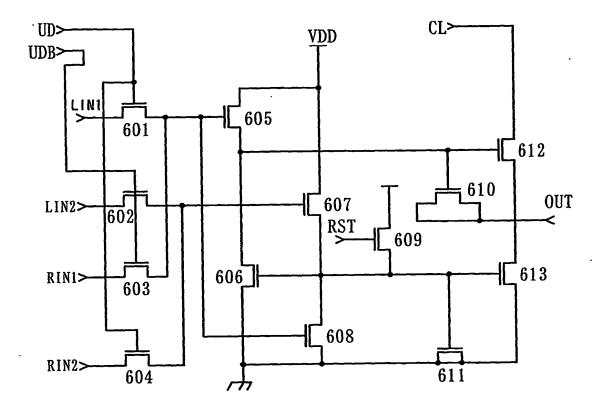
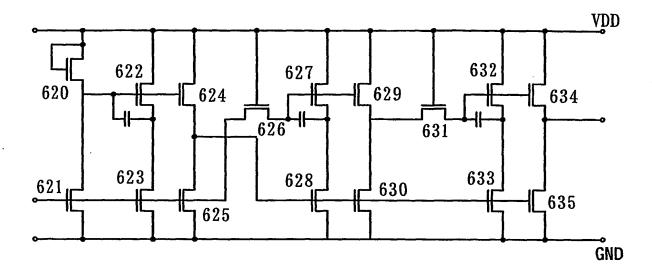
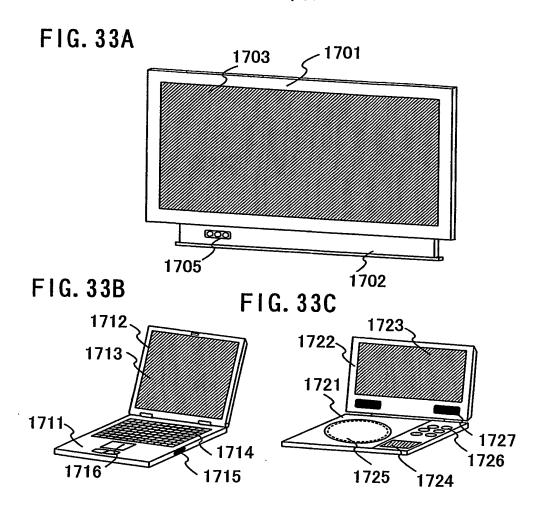
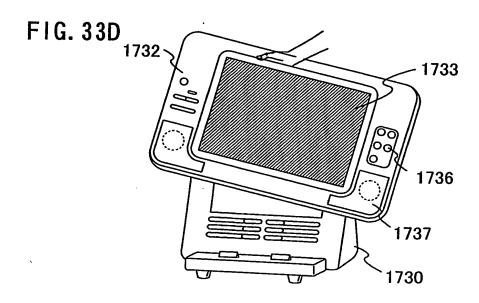


FIG. 32







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#### EXPLANATION OF REFERENCE

10: substrate, 11: base layer, 12: conductive pattern, 15: gate electrode, 17: leading out electrode, 18: gate insulating film, 19: semiconductor film, 20: semiconductor film, 32; mask, 22: source wiring or drain wiring, 23: source wiring or drain wiring, 24: channel formation region, 25: drain region, 26: source region, 27: protective film, 28: interlayer insulating film, 29: convex portion (pillar), 30: first electrode, 34: bank, 35: sealing substrate, 36: layer containing an organic compound, 37: second electrode, 38: filler, 40: wiring, 41: terminal electrode, 45: anisotropic conductive film, 46: FPC, 220: conductive film pattern, 221: portion irradiated with laser light, 222: source wiring or drain wiring. 223: drain region, 226: source region, 250: conductive pattern, 251: portion irradiated with laser light, 252: source wiring or drain wiring, 253: source wiring or drain wiring, 254: channel formation region, 255: drain region, 256: source region, 260: gate insulating film, 260: gate insulating film, 301: base insulating film, 302: gate electrode, 320: conductive film pattern, 322: source wiring or drain wiring, 323: source wiring or drain wiring, 324; channel formation region, 325: drain region, 326: source region, 401: laser beam directly drawing device, 402: personal computer, 403: laser oscillator, 404: power source, 405: optical system, 406: sound optical modulator, 407: optical system, 408: substrate, 409: substrate, 410: D/A converter, 411: driver, 412: driver, 500: pulse output circuit, 501: buffer circuit, 502: pixel, 601: n-channel TFT, 602: n-channel TFT, 603: n-channel TFT, 604: n-channel TFT, 608: n-channel TFT, 609: n-channel TFT, 610: n-channel TFT, 611: n-channel TFT, 612: n-channel TFT, 613, 620: n-channel TFT, 621: n-channel TFT, 622: n-channel TFT, 623: n-channel TFT, 624: n-channel TFT, 625: n-channel TFT, 626: n-channel TFT, 627: n-channel TFT, 628: n-channel TFT, 629: n-channel TFT,630: n-channel TFT,631: n-channel TFT, 632: n-channel TFT, 633: n-channel TFT, 634: n-channel TFT, 635: n-channel TFT, 700: substrate, 701: pixel portion, 702: pixel, 703: scanning line side input terminal, 704: signal line side input terminal, 810: substrate, 811: base film, 815: gate electrode, 818: gate insulating film, 822: wiring, 823: wiring, 824: semiconductor film, 825: wiring, 826: n-type semiconductor film, 827: channel protective film, 828: interlayer insulating film, 829: electrode, 830: electrode, 840; terminal electrode, 841: electrode, 910: substrate, 911:

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base film, 915: gate wiring, 918: gate insulating layer, 923: source wiring layer, 924: source wiring layer, 925: n-type semiconductor layer, 926: n-type semiconductor layer, 927: semiconductor layer, 928: interlayer insulating film, 929: electrode, 930: electrode, 940: terminal electrode, 941: electrode, 1031: second substrate, 1032: sealant, 1033: liquid crystal, 1034: pixel portion, 1035: first substrate, 1041: first substrate support medium, 1042: second substrate support medium, 1044: window, 1048: lower surface table, 1049: light source, 1110: large substrate, 1111: pixel portion, 1112: sealant, 1113: nozzle scanning direction, 1114: liquid crystal material, 1115: dropped surface, 1116: droplet discharging device, 1118: nozzle, 1119: portion denoted by dotted line, 1120: reverse staggered TFT, 1121: pixel electrode, 1200: sealant, 1201: active matrix substrate, 1202: sealing substrate, 1203: pixel portion, 1204: space, 1205: 1/4λ plate and 1/2λ plate, 1206: polarized plate, 1207: colored layer, 1208: connecting terminal, 1209: FPC, 1210: printed substrate, 1211: pixel driver circuit, 1212: external circuit, 1221: protective film, 1301: driving TFT, 1302: insulating film, 1303: electroluminescent layer, 1304: second electrode, 1305: emitting direction, 1306: both arrows direction, 1310: driver circuit portion, 1311: pixel portion, 1401: switching TFT, 1402: capacitor element, 1403: driving TFT, 1404: current control TFT, 1405: light-emitting element, 1406: TFT, 1410: signal line, 1411: power line, 1412: power line, 1413: power line, 1414: scanning line, 1415: power line, 1441: switching TFT, 1442: capacitor element, 1443: driving TFT, 1444: light-emitting element, 1445: TFT, 1450: signal line, 1451: power line, 1452: power line, 1453: scanning line, 1454: scanning line, 1500: large substrate, 1503: region, 1504: imaging means, 1505a: head, 1505b: head, 1505c: head, 1507: stage, 1511: marker, 1600: substrate, 1601: pixel region, 1602: scanning line driver circuit, 1604a, 1604b, and 1605a: driver circuit, 1605b: driver circuit, 1701: housing, 1702: support medium, 1703: display portion, 1705: video input terminal, 1711: main body, 1712: housing, 1713: display portion, 1714: key board, 1715: external connecting port, 1716: pointing mouse, 1721: main body, 1722: housing, 1723: display portion A, 1724: display portion B, 1725: recording medium reading portion, 1726: operation keys, 1727: speaker portion, 1730: charger, 1732: housing, 1733: display portion, 1736: operation keys, 1737: speaker portion, 1800: active matrix substrate, 1801: opposing substrate, 1802: sealant, 1803:

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pixel region, 1804: drying agent, 1805: source wiring, 1806: gate wiring, 1807: pixel, 1811: pixel, 1812: pixel electrode, 1814: drying agent, 2010: substrate, 2011: base substrate, 2012: conductive film pattern, 2015: gate wiring, 2018: gate insulating film, 2019: semiconductor film, 2020: semiconductor film, 2021: mask, 2022: source wiring or drain wiring, 2023: source wiring or drain wiring, 2024: channel formation region, 2025: drain region, 2026: source region, 2027: protective film, 2028: interlayer insulating film, 2029: convex portion (pillar), 2030: pixel electrode, 2034a: oriented film, 2034b: oriented film, 2035: opposing substrate, 2036a: colored layer, 2036b: light-shielding film (black matrix), 2037: overcoat layer, 2038, 2039: liquid crystal, 2040: wiring, 2045: anisotropic conductive layer, 2046: FPC, 2120: conductive film pattern, 2121: portion irradiated with laser light, 2122: source wiring or drain wiring, 2123: source wiring or drain wiring, 2124: channel formation region, 2125: drain region, 2126: source region, 2150: conductive pattern, 2151: portion irradiated with laser light, 2152: source wiring or drain wiring, 2153: source wiring or drain wiring, 2154: channel formation region, 2155: drain region, 2156: source region, 2160: gate insulating film, 2201: base insulating film, 2202: gate electrode, 2220: conductive film pattern, 2222: source wiring or drain wiring, 2223: source wiring or drain wiring, 2224: channel formation region, 2225: drain region, 2226: source region, 2310: substrate, 2311: base insulating, 2315: gate electrode, 2318: gate insulating film, 2322: wiring, 2323: wiring, 2324: semiconductor film, 2325: n-type semiconductor film, 2326: n-type semiconductor film, 2627: channel protective film, 2328: interlayer insulating film, 2329: electrode, 2330: electrode, 2340: terminal electrode, 2341: electrode, 2410, 2411: base film, 2415: gate wiring, 2418: gate insulating layer, 2423: source wiring layer, 2424: drain wiring layer, 2425: n-type semiconductor, 2426: n-type semiconductor, 2427: semiconductor layer, 2428: interlayer insulating film, 2429: electrode, 2430: electrode, 2440: terminal electrode, 2441: electrode, 2501: substrate, 2504: pixel portion, 2505: FPC, 2506: opposing substrate, 2507: sealant, 2511: substrate, 2512: source signal line driver circuit, 2513: gate signal line driver circuit, 2514: pixel portion, 2515: FPC, 2516: opposing substrate, 2517: sealant, 2518: second sealant, 2600: substrate, 2601: pixel electrode, 2602: spacer, 2603: polarized plate, 2604: backlight valve, 2606: cover, 2607: sealant, 2620: CF, 2621:

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opposing electrode, 2622: oriented film, 2623: oriented film, 2624: liquid crystal layer, 2625: planarized film.